



DOCUMENT CHANGE REQUEST

DCR number	442	Changes required for:	General	Originator:	S Jeffery - ESCC
Date:	2008/11/05	Date sent:	2008/11/05	Organisation:	
Status:	IMPLEMENTED				

Title: Transistors Low Power PNP, based on types 2N2894 and 2N2894A

Number:	5202/004	Issue:	1
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Other documents affected:

Page:

Total Re-write.

Paragraph:

Total Re-write.

Original wording:

Proposed wording:

Total reformat of this specification as part of the ongoing conversion to the ESCC format. See below for summary of changes and attached Issue 2 Draft A of the specification.

Note: known support for active procurement against this specification includes the following manufacturers:

SEMELAB/UK (not ESCC qualified but are currently willing to support the procurement of Variants 01 to 07)

Summary of changes to the current format, layout and content is as follows:

1. Rewording and restructuring of various sections and paragraphs of the specification, plus other editorial changes based on the layout and editorial content of other Detail Specifications already converted to ESCC format.
2. Deletion of redundant paragraphs and information such as Mechanical Requirements.
3. Para. 1.7 High Temperature Test Precautions requirements moved to be a note to the Maximum Ratings table.
4. Maximum Ratings table: Notes 2 and 1 interchanged.
5. Figure 1 Parameter Derating Information moved to be a note to the maximum Ratings table ("Note 1" amended).
6. Para. 4.3.2 Weight requirements moved to Component Type Variants table.
7. Figure 2 re-named "Physical Dimensions and Terminal Identification" and amended to reflect the TO-18 and CCP packages currently supplied.



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8. Figure 3, Functional Diagram: A note applicable to the Chip Carrier Package (Note 2) has been added.
9. Para. 4.4.1 Case requirements for Variants 01 to 05 corrected to reflect a TO-18 metal can.
10. Para. 4.4.2 Lead Material and Finish replaced by a reference to the Component Type Variants Para.
11. Delete requirement for marking of the test level letter from the ESCC Component Number as per latest ESCC No. 21700.
12. Table 2, Characteristic Collector-Base Breakdown Voltage: reference to Note 1 deleted.
13. Table 2, Characteristic Emitter-Base Breakdown Voltage: Limit corrected (was -4.5V min, now -4V min).
14. Table 2, Characteristics "D.C. Forward Current Transfer Ratio 1", "D.C. Forward Current Transfer Ratio 2", and "D.C. Forward Current Transfer Ratio 3" combined and re-named "Forward-Current Transfer Ratio".
15. Table 2, Characteristics "Collector-Emitter Saturation Voltage 1", "Collector-Emitter Saturation Voltage 2" and "Collector-Emitter Saturation Voltage 3" combined and re-named "Collector-Emitter Saturation Voltage".
16. Table 2, Characteristics "Base-Emitter Saturation Voltage 1" and "Base-Emitter Saturation Voltage 2" combined and re-named "Base-Emitter Saturation Voltage".
17. Table 2, Characteristic "High Frequency Current Gain" re-named "Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio"; Symbol amended (was hfe, now |hfe|).
18. Table 2, Characteristic "Emitter Transition Capacitance" re-named "Input Capacitance"; MIL-STD-750 Test Method corrected from 3236 to 3240; IC = 0A Test Condition added.
19. Table 2: Figure 4 deleted and incorporated in to a Note to Table 2 (Note 3).
20. Table 2: Replace LTPD7 sampling for AC parameters tests (designated by "Note 2") with an equivalent fixed sample of 32 components with 0 failures (or 100%).
21. Table 3, Characteristic "D.C. Forward Current Transfer Ratio 2" re-named "Forward-Current Transfer Ratio 2".
22. Table 3 (High and Low Temperatures Electrical Measurements): 100% inspection has been replaced by a sample of 5 components with 0 failures, or 100%, in line with the new Generic 5000 Issue 3.
23. Table 4: Absolute limits have been added for information.
24. Table 4, Characteristic "D.C. Forward Current Transfer Ratio 2" re-named "Forward-Current Transfer Ratio 2".



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25. Tables 2, 3 and 4 - Test Conditions column: addition of Test, or Bias, Conditions for referenced MIL-STD-750 Test Methods as and where applicable.

26. Table 5(a) Test Conditions for High Temperature Reverse Bias amended: Tamb was +150 Deg.C, now +150 (+0 - 5)Deg.C; Duration was 72 hours, now 72 hours minimum, in line with new Generic 5000 and MIL specifications.


27. Table 5(b): Characteristic "Power Dissipation 1" re-named "Power Dissipation"; Tamb was +25 Deg.C, now +20 to +50 Deg.C; Test Conditions for Power Dissipation amended/re-written and Note 1 deleted; Symbol Ptot1 amended to Ptot.

28. Table 6, Characteristic "D.C. Forward Current Transfer Ratio 2" re-named "Forward-Current Transfer Ratio 2".

Justification:

(see also change details for each item above)

1. Part of the ongoing activity of conversion of cover-sheeted ESA/SCC Specifications to the ESCC format.
2. To make the format and presentation consistent with the various other ESCC Detail Specifications already converted to ESCC format.
3. To make the content consistent with ESCC Generic Specification No. 5000 Issue 3.
4. To make corrections to technical errors in the previous issue.
5. Standardisation of the TO-18 and CCP packages in all applicable ESCC Detail Specifications.

Attachments:
5202004.pdf, null
Modifications:
N/A
Approval signature:

Date signed:
2008-11-05



Pages 1 to 16

TRANSISTORS, LOW POWER, PNP

BASED ON TYPE 2N2894 and 2N2894A

ESCC Detail Specification No. 5202/004

Issue 2	January 2009
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DCR No.	CHANGE DESCRIPTION
442	Specification up issued to incorporate editorial and technical changes per DCR.

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1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520200401

- Detail Specification Reference: 5202004
- Component Type Variant Number: 01 (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g
01	2N2894	TO-18	D2	0.4
02	2N2894	TO-18	D2	0.4
03	2N2894	TO-18	D3 or D4	0.4
04	2N2894	TO-18	D3 or D4	0.4
05	2N2894	TO-18	D7	0.4
06	2N2894	CCP	2	0.06
07	2N2894	CCP	4	0.06

The lead/terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 **MAXIMUM RATINGS**

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V_{CBO}	-12	V	Over entire operating temperature range
Collector-Emitter Voltage	V_{CEO}	-12	V	
Emitter-Base Voltage	V_{EBO}	-4	V	
Collector Current	I_C	-200	mA	Continuous
Power Dissipation For TO-18 and CCP For CCP For TO-18	P_{tot1}	0.36	W	At $T_{amb} \leq +25^{\circ}C$ Note 1
	P_{tot2}	0.58 (Note 2)	W	
	P_{tot3}	1.2	W	At $T_{case} \leq +25^{\circ}C$ Note 1
Operating Temperature Range	T_{op}	-65 to +200	$^{\circ}C$	Note 3
Storage Temperature Range	T_{stg}	-65 to +200	$^{\circ}C$	Note 3
Soldering Temperature For TO-18 For CCP	T_{sol}	+260	$^{\circ}C$	Note 4
		+245		Note 5

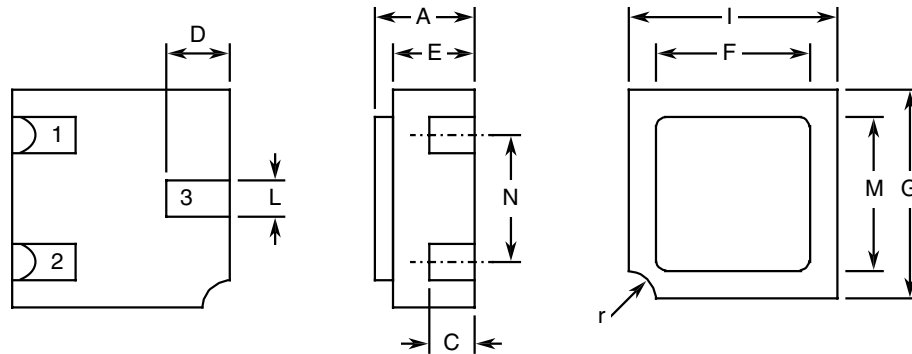
NOTES:

- For T_{amb} or $T_{case} > +25^{\circ}C$, derate linearly to 0W at +200 $^{\circ}C$.
- When mounted on a 15 x 15 x 0.6mm ceramic substrate.
- For Variants with tin-lead plating or hot solder dip lead finish all testing, and any handling, performed at $T_{amb} > +125^{\circ}C$ shall be carried out in a 100% inert atmosphere.
- Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

below the seating plane of the device shall be within 0.178mm of their true position relative to a maximum-width-tab.

5. Measured from the maximum diameter of the actual device.
6. Tab centreline.

1.6.2 Chip Carrier Package (CCP) - 3 terminal

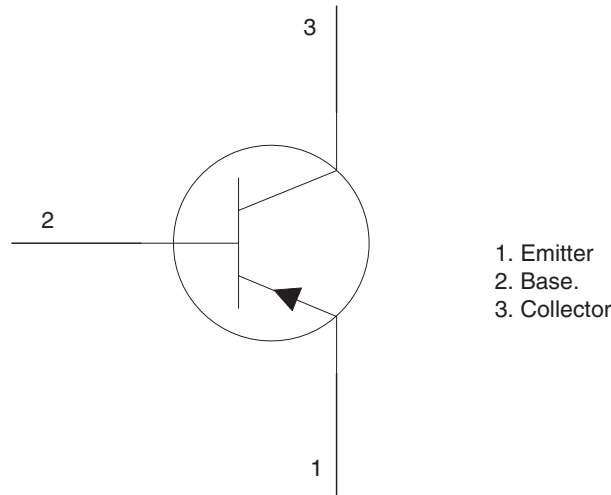


Symbols	Dimensions mm		Notes
	Min	Max	
A	1.15	1.5	
C	0.45	0.56	2
D	0.6	0.91	2
E	0.91	1.12	
F	1.9	2.15	
G	2.9	3.25	
I	2.4	2.85	
L	0.4	0.6	2
M	2.4	2.65	
N	1.8	2	
r	0.3 TYPICAL		1

NOTES:

1. Terminal identification is specified by reference to the corner notch position where terminal 1 = emitter, terminal 2 = base, terminal 3 = collector.
2. Applies to all terminals.

1.7 FUNCTIONAL DIAGRAM



NOTES:

1. For TO-18, the collector is internally connected to the case.
2. For CCP, the lid is not connected to any terminal.

1.8 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

- a) Case
For the metal can package the case shall be hermetically sealed and have a metal body with hard glass seals.

For the chip carrier package the case shall be hermetically sealed and have a ceramic body with a Kovar lid.
- b) Leads/Terminals
As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

None.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number.
- (c) Traceability information.

2.3 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

For TO-18, Test Condition: E, lead fatigue.

2.4 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.4.1 Room Temperature Electrical Measurements

The measurements shall be performed at $T_{amb}=+22 \pm 3^{\circ}\text{C}$.

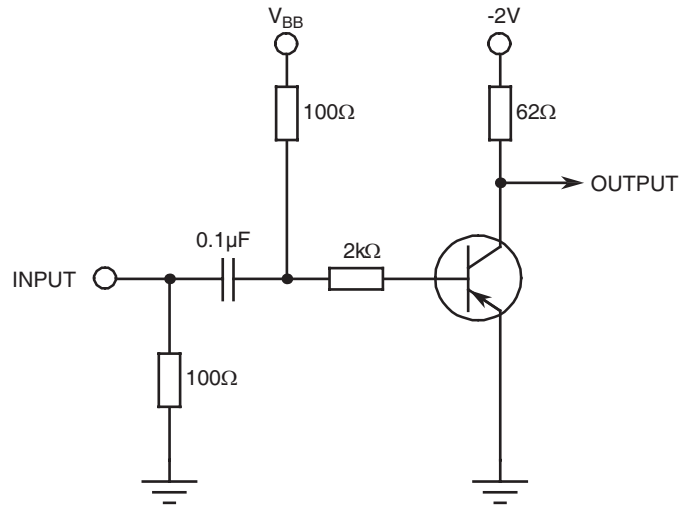
Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	$I_C = -10mA$ Note 1 Bias condition D	-12	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	3001	$I_C = -10\mu A$ Bias condition D	-12	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	$I_E = -100\mu A$ Bias condition D	-4	-	V
Collector-Base Cut-off Current	I_{CBO}	3036	$V_{CB} = -10V$ Bias condition D	-	-100	nA
Forward-Current Transfer Ratio	h_{FE1}	3076	$V_{CE} = -300mV$; $I_C = -10mA$ Note 1 2N2894 2N2894A	30 -	- -	-
	h_{FE2}	3076	$V_{CE} = -500mV$; $I_C = -30mA$ Note 1 2N2894 2N2894A	40 40	150 120	-
	h_{FE3}	3076	$V_{CE} = -1V$; $I_C = -100mA$ Note 1 2N2894 2N2894A	25 30	- -	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	3071	$I_C = -10mA$ $I_B = -1mA$ Note 1 2N2894 2N2894A	- -	-150 -	mV
	$V_{CE(sat)2}$	3071	$I_C = -30mA$ $I_B = -3mA$ Note 1 2N2894 2N2894A	- -	-200 -190	mV
	$V_{CE(sat)3}$	3071	$I_C = -100mA$ $I_B = -10mA$ Note 1 2N2894 2N2894A	- -	-500 -450	mV

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Base-Emitter Saturation Voltage	$V_{BE(sat)1}$	3066	$I_C = -10mA$ $I_B = -1mA$ Note 1 Test condition A 2N2894 2N2894A	-780 -	-980 -	mV
	$V_{BE(sat)2}$	3066	$I_C = -30mA$ $I_B = -3mA$ Note 1 Test condition A 2N2894 2N2894A	-0.85 -	-1.2 -1.15	V
Magnitude of Small-Signal Short-Circuit Forward-Current Transfer Ratio	$ h_{fe} $	3306	$V_{CB} = -30mA,$ $V_{CE} = -10V$ $f = 100MHz$ Note 2 2N2894 2N2894A	4 7	- -	-
Output Capacitance	C_{obo}	3236	$V_{CB} = -5V,$ $I_E = 0A$ $f = 1MHz$ Note 2 2N2894 2N2894A	- -	6 4.5	pF
Input Capacitance	C_{ibo}	3240	$V_{EB} = -500mV$ $I_C = 0A$ $f = 1MHz$ Note 2	-	6	pF
Turn-on Time	t_{on}	-	$V_{BB} = 3V, V_{IN} = -7V,$ $I_C = -30mA$ $I_{BL} = 1.5mA$ Notes 2, 3 2N2894 2N2894A	- -	60 40	ns
Turn-off Time	t_{off}	-	$V_{BB} = -4V, V_{IN} = 6V,$ $I_C = -30mA$ $I_{B1} = I_{B2} = 1.5mA$ Notes 2, 3 2N2894 2N2894A	- -	90 60	ns

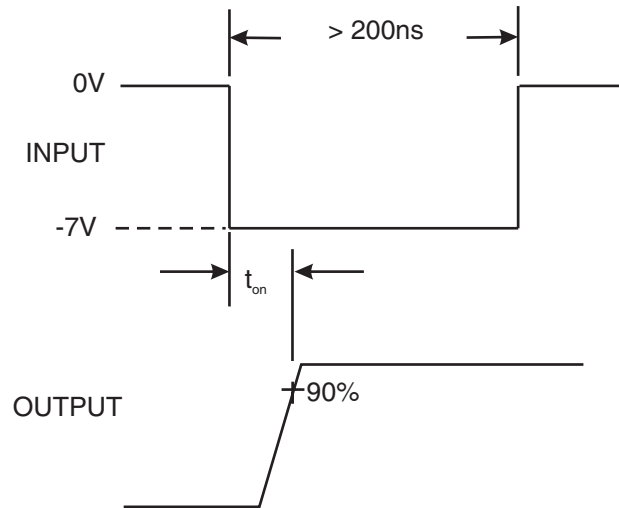
NOTES:

1. Pulse measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
2. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
3. t_{on} shall be measured using the following test circuit. The input waveform shall be supplied by a pulse generator with the following characteristics: $Z_{OUT} = 50\Omega$, $t_r \leq 2ns$, Pulse Width = $200 \pm 10ns$, Duty Cycle $\leq 2\%$. The output waveform shall be monitored on an oscilloscope with the following

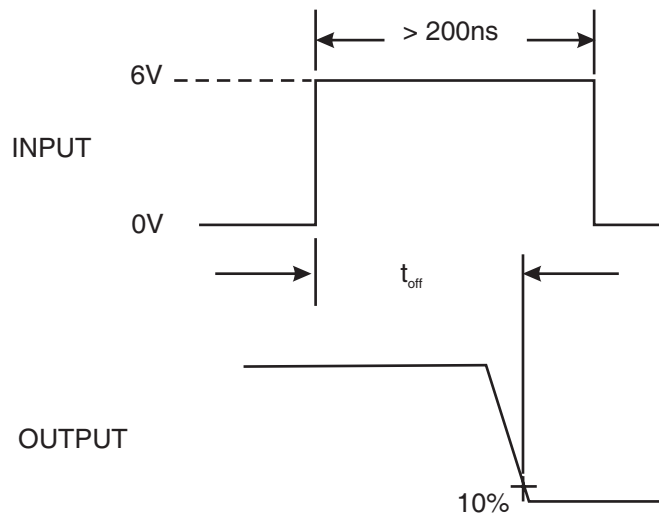
characteristics: $Z_{IN} \geq 100k\Omega$, input capacitance $\leq 12pF$, $t_r \leq 1ns$.



VOLTAGE WAVEFORM FOR t_{on}



VOLTAGE WAVEFORM FOR t_{off}



2.4.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Collector-Base Cut-off Current	I_{CBO}	3036	$T_{amb}=+150 (+0 -5)^{\circ}C$ $V_{CB}=-50V$ Bias condition D	-	-10	μA
Forward-Current Transfer Ratio 2	h_{FE2}	3076	$T_{amb}=-55 (+5 -0)^{\circ}C$ $V_{CE}=-500mV$ $I_C=-30mA$ Note 2	20	-	-

NOTES:

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.
2. Pulsed measurement: Pulse Width $\leq 300\mu s$, duty Cycle $\leq 2\%$.

2.5 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb}=+22 \pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Collector-Base Cut-off Current	I_{CBO}	± 20 or (1) $\pm 100\%$	-	-10	nA
Forward-Current Transfer Ratio 2 2N2894 2N2894A	h_{FE2}	$\pm 15\%$	40 40	150 150	-
Collector-Emitter Saturation Voltage 3 2N2894 2N2894A	$V_{CE(sat)}$	± 50 or (1) $\pm 15\%$	-	-500 -450	mV

NOTES:

1. Whichever is the greater referred to initial value.

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{amb}=+22 \pm 3^{\circ}\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Base Cut-off Current	I_{CBO}	-	-100	nA
Forward-Current Transfer Ratio 2 2N2894 2N2894A	h_{FE2}	40 40	150 150	-
Collector-Emitter Saturation Voltage 3 2N2894 2N2894A	$V_{CE(sat)}$	- -	-500 -450	mV

2.7 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150 (+0 -5)	$^{\circ}\text{C}$
Collector-Base Voltage	V_{CB}	12	V
Duration	t	72 minimum	Hours

2.8 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+20 to +50	$^{\circ}\text{C}$
Power Dissipation	P_{tot}	As per Maximum Ratings P_{tot1} derated at the chosen T_{amb}	W
Collector-Base Voltage	V_{CB}	-10	V

2.9 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.